

EAST - (thinsearch15.wsp:1)

File View Edit Tools Window Help

☐ BRS: ferronagnetic and offset
☐ BRS: 1 2
☐ BRS:
☐ BRS:
☐ BRS: upside
☒ Pending
☒ Active
☐ L2: (64) nitride adj memory
☐ L1: (382) NROM
☐ L3: (285) 1 and nitride
☐ L4: (47278) bit adj line
☐ L5: (175) 3 and 4
☒ Failed
☐ (0) AND adi logic

DBs: SUBPAT, US PGPUB, EPD, JPD, DERWENT, IBM, YDB
 Display options: OR
 3 and 4

BRS: 30ms BRS: 50ms Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Clu	Inventor	S	C	P	3	Image 1
1			US 20030185071	20031002	24	Nonvolatile semiconductor memory device and method of manufacturing	365/200			Yoshino, Akira					US 2003
2			US 20030185053	20031002	16	Fast program to program verify method	365/185.18			Ogura, Seiki et al.					US 2003
3			US 20030174570	20030918	43	Semiconductor memory device having potential control circuit	365/230.03			Ooishi, Tsukasa					US 2003
4			US 20030161183	20030828	120	Digital multilevel non-volatile memory system	365/185.03	365/185.2		Tran, Hieu Van					US 2003
5			US 20030157758	20030821	73	Non-volatile semiconductor memory device and manufacturing method the	438/199			Ohtani, Jun et al.					US 2003
6			US 20030155607	20030821	87	SEMICONDUCTOR INTEGRATED CIRCUIT	257/324			Kamigaki, Yoshiaki et al.					US 2003
7			US 20030151946	20030814	46	Nonvolatile semiconductor memory device having control circuit	365/185.03			Ooishi, Tsukasa					US 2003
8			US 20030145176	20030731	28	Mass storage device architecture and operation	711/154	711/104; 711/162		Dvir, Ran et al.					US 2003
9			US 20030142544	20030731	24	Mass storage array and methods for operation thereof	365/185.16			Maayan, Eduardo et al.					US 2003
10			US 20030141532	20030731	23	Non-volatile semiconductor memory device of which bit line withstand volt	257/304			Kato, Hiroshi					US 2003
11			US 20030134478	20030717	10	Non-volatile memory and fabrication thereof	438/275	438/278; 438/291		Lai, Han-Chao et al.					US 2003
12			US 20030134476	20030717	9	Oxide-nitride-oxide structure	438/261			Roizin, Yakov et al.					US 2003
13			US 20030132488	20030717	10	Non-volatile memory and fabrication thereof	257/390	257/391		Lai, Han-Chao et al.					US 2003
14			US 20030128588	20030710	16	Fast program to program verify method	365/185.18	365/185.21; 365/189.07		Ogura, Seiki et al.					US 2003
15			US 20030123308	20030703		Fast program to program verify method	365/200			Ogura, Seiki et al.					
16			US 20030123293	20030703		Fast program to program verify method	365/185.18			Ogura, Seiki et al.					
17			US 20030123292	20030703		Fast program to program verify method	365/185.18			Ogura, Seiki et al.					

Ready

CAP NUM